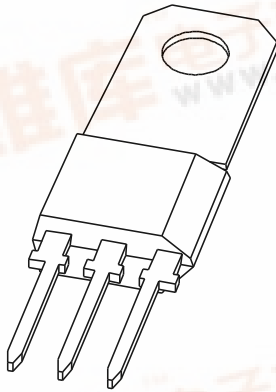


DISCRETE SEMICONDUCTORS

DATA SHEET



BF583; BF585; BF587 NPN high-voltage transistors

Product specification

1996 Dec 09

Supersedes data of September 1994

File under Discrete Semiconductors, SC04

NPN high-voltage transistors

BF583; BF585; BF587

FEATURES

- Low feedback capacitance.

APPLICATIONS

- For use in video output stages of black and white and colour television receivers.

DESCRIPTION

NPN transistors in a TO-202 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base

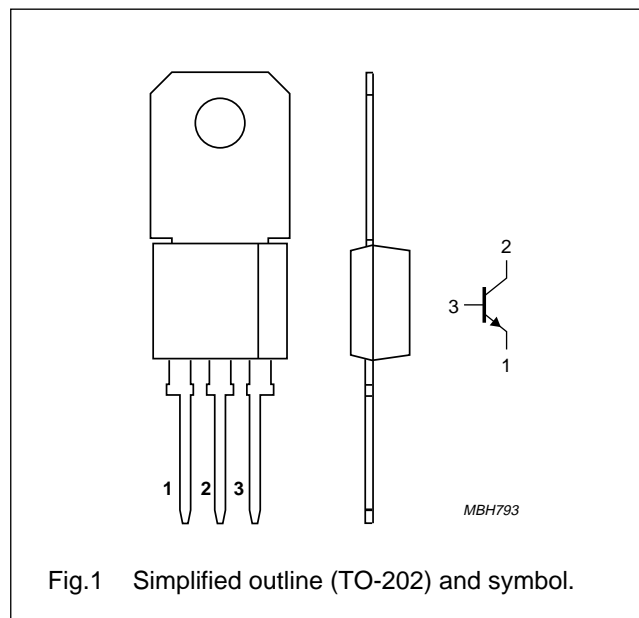


Fig.1 Simplified outline (TO-202) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BF583		–	300	V
	BF585		–	350	V
	BF587		–	400	V
V_{CEO}	collector-emitter voltage	open base			
	BF583		–	250	V
	BF585		–	300	V
	BF587		–	350	V
I_{CM}	peak collector current		–	100	mA
P_{tot}	total power dissipation	in free air; $T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	1.6	W
h_{FE}	DC current gain	$I_C = 25\text{ mA}$; $V_{CE} = 20\text{ V}$	–	50	
C_{re}	feedback capacitance	$I_C = i_c = 0$; $V_{CE} = 30\text{ V}$; $f = 1\text{ MHz}$	–	1.8	pF
f_T	transition frequency	$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$	70	110	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF583		–	300	V
	BF585		–	350	V
	BF587		–	400	V
V _{CEO}	collector-emitter voltage	open base			
	BF583		–	250	V
	BF585		–	300	V
	BF587		–	350	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		50	–	mA
I _{CM}	peak collector current		–	100	mA
I _{BM}	peak base current		–	50	mA
P _{tot}	total power dissipation	in free air; T _{amb} ≤ 25 °C	–	1.6	W
		in free air; T _{mb} ≤ 25 °C	–	5	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	78	K/W
R _{th j-mb}	thermal resistance from junction to mounting base	25	K/W

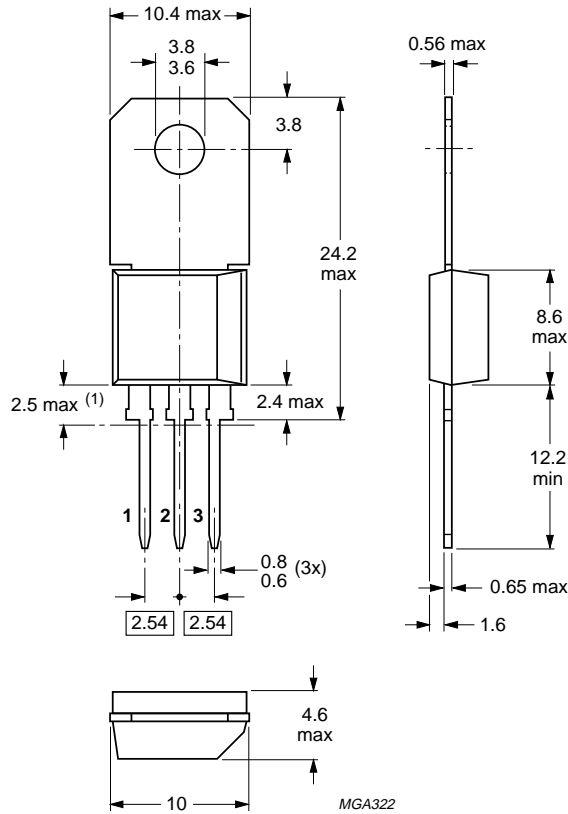
CHARACTERISTICST_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 300 V	–	20	nA
		I _E = 0; V _{CB} = 250 V; T _j = 150 °C	–	20	μA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	–	100	nA
h _{FE}	DC current gain	I _C = 25 mA; V _{CE} = 20 V	50	–	
		I _C = 40 mA; V _{CE} = 20 V	20	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 30 mA; I _B = 5 mA	–	600	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 30 V; f = 1 MHz	–	2.5	pF
C _{re}	feedback capacitance	I _C = i _c = 0; V _{CE} = 30 V; f = 1 MHz	–	1.8	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V	70	110	MHz

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PACKAGE OUTLINE



Dimensions in mm.

(1) Terminal dimensions within this zone are uncontrolled.

Fig.2 TO-202.

NPN high-voltage transistors

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NOTES

NPN high-voltage transistors

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NOTES

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